风光欣技术资料

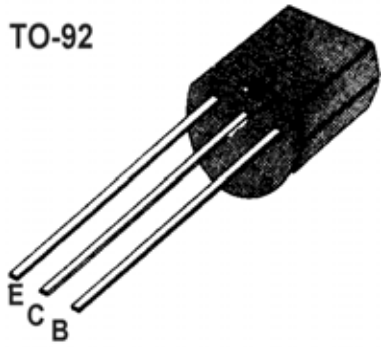
A1317

—PNP silicon —

■■**APPLICATION**：Loe frequency Amplifier Application.

■■**MAXIMUM RATINGS**（Ta＝25℃）

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CBO}	-60	V
Collector-emitter voltage	V_{CEO}	-50	V
Emitter-base voltage	V_{EBO}	-6	V
Collector current	I_C	-200	mA
Collector Power Dissipation	P_C	300	mW
Junction Temperature	T_J	150	℃
Storage Temperature Range	Tstg	－55~150	℃



■■**ELECTRICAL CHARACTERISTICS**（Ta=25℃）

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
Common Emitter DC Current Gain	h_{FE}	100		560		V_{CE}= -6V，Ic= -1mA
Collector Cut-off Current	I_{CBO}			-0.1	μA	V_{CB}= -40V，I_E=0
Emitter Cut-off Current	I_{EBO}			-0.1	μA	V_{EB}= -5V，Ic=0
Collector-Base Breakdown Voltage	BV_{CBO}	-60			V	Ic= -0.1mA，I_E=0
Collector-Emitter Breakdown Voltage	BV_{CEO}	-50			V	Ic= -1mA，I_B=0
Emitter-Base Breakdown Voltage	BV_{EBO}	-6			V	I_E= -0.1mA，Ic=0
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.3	V	Ic= -100mA，I_B= -10mA
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			-1.0	V	Ic= -100mA，I_B= -10mA
Gain bandwidth product	f_T		200		MHz	Ic= -10mA，V_{CE}= -6V
Common Base Output Capacitance	Cob		3.0		PF	V_{CB}= -6V，I_E=0，f = 1MHz

■■h_{FE} **Classification**

Classification	R	S	T	U
h_{FE}	100~200	140~280	200~400	280~560